## North South University Department of Electrical and Computer Engineering EEE/ETE 111L Fall 2021 Quiz 02

ANSWER ALL THE QUESTION Total Marks: 25 (Time: 30 Minutes)

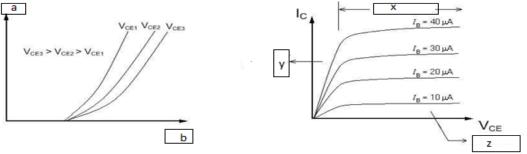
## N.B.: Write each formula clearly. Don't forget to use correct unit!

experiment.

The characteristics of a BJT transistor are measured by two characteristics curve (Figure: A)

 Write the name of the two curves given below.
 What are the name of the variables, a, b, x, y, z in the curves given below?

 What is the function of a BJT?



## Figure: A

2

- 2. Consider the circuit of Figure B.

  a. What do you understand by "Biasing a BJT circuit"?
  b. What are the names of the circuits (Fig. B)?
  c. Draw the symbol of the transistor used in the circuit with proper labelling.
  d. During the lab experiment which circuit showed better stability?
  e. Mention TWO differences between BJT and MOSFET you observed during
  - $R_{B1} \ge 10 \text{ K}\Omega \qquad R_{C} \ge 470 \text{ }\Omega$   $R_{B2} \ge 10 \text{ K}\Omega \qquad 8560 \text{ }\Omega$   $R_{B2} \ge 10 \text{ K}\Omega \qquad 8560 \text{ }\Omega$

Figure: B

3. What is the name of the equipment of given below? What are the function of A, D, and E? (A $\rightarrow$  cursor, D $\rightarrow$  Volt/Div, E $\rightarrow$  Sec/Div)  $\frac{4 \text{ pts}}{1+3}$ 

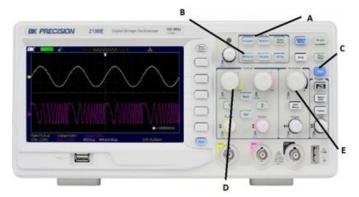


Figure: C

4. What is the name of the graph given below? From the experiment explain how does a MOSFET work in the three working region mentioned in the graph?

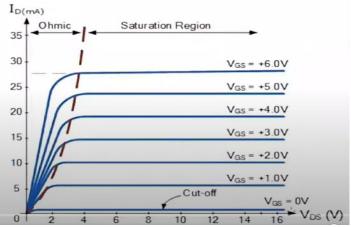


Figure: D

5. True/ false and Fill in the blanks:

h of  $\frac{4 \text{ pts}}{1}$ 

2

3 pts

1+2

- a. When forward biased voltage is applied to the p-n junction diode, the width of depletion region decreases. ( )
- b. BJT is a current controlled device whereas MOSFET is a voltage controlled device. ( )